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🔍 Title: **JP57176771A2: SEMICONDUCTOR MEMORY DEVICE**

🔍 Country: **JP Japan**

🔍 Kind: **A**

🔍 Inventor: **OSADA YOSHIHIRO;**

🔍 Assignee: **MITSUBISHI ELECTRIC CORP**  
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🔍 Published / Filed: **1982-10-30 / 1981-04-23**

🔍 Application Number: **JP1981000062913**

🔍 IPC Code: **H01L 29/78; G11C 11/40; H01L 27/10;**

🔍 Priority Number: **1981-04-23 JP1981000062913**

🔍 Abstract:

PURPOSE: To obtain a memory element having excellent surface protecting property, by providing a double layer structure comprising a first layer through which ultraviolet rays are transmitted and a second film through which the ultraviolet rays are not transmitted but which has the excellent surface protecting property, as a surface protecting film, and removing the parts of the second film which are required to irradiate the ultraviolet rays.

CONSTITUTION: In a floating gate type memory device, an SiO<sub>2</sub> film 8 through which the ultraviolet rays are transmitted in order to erase the charge in the floating gate and an Si<sub>3</sub>N<sub>4</sub> film 9 through which the ultraviolet rays are not transmitted but which has the excellent surface protecting property are deposited on the entire surface. The specified parts of the Si<sub>3</sub>N<sub>4</sub> film are selectively removed so that the ultraviolet rays can be transmitted. In this constitution, the function as the memory device is accomplished and the surface protecting characteristic becomes excellent.

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🔍 Family: **None**

Other Abstract  
Info: **None**



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